

## Description

The 4N29, 4N30, 4N31, 4N32, 4N33 H11B1, H11B2, H11B3, H11B255 series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar darlington phototransistor detector in a plastic DIP6 package with different lead forming options

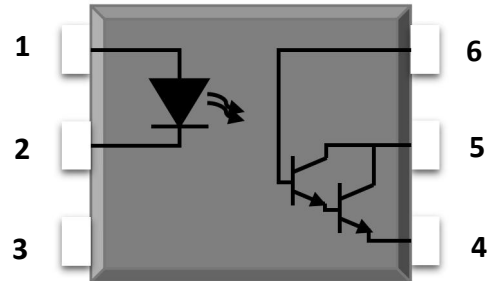
## Features

- High isolation 5000 VRMS
- DC input with transistor output
- Operating temperature range - 55 °C to 110 °C
- RoHS & REACH Compliance
- MSL class 1
- Regulatory Approvals
  - UL - UL1577
  - VDE - EN60747-5-5(VDE0884-5)
  - CQC - GB4943.1, GB8898
  - cUL- CSA Component Acceptance Service Notice No. 5A

## Applications

- Low power logic circuits
- Telecommunications equipment
- Portable electronics
- Interfacing coupling systems of different potentials and impedances

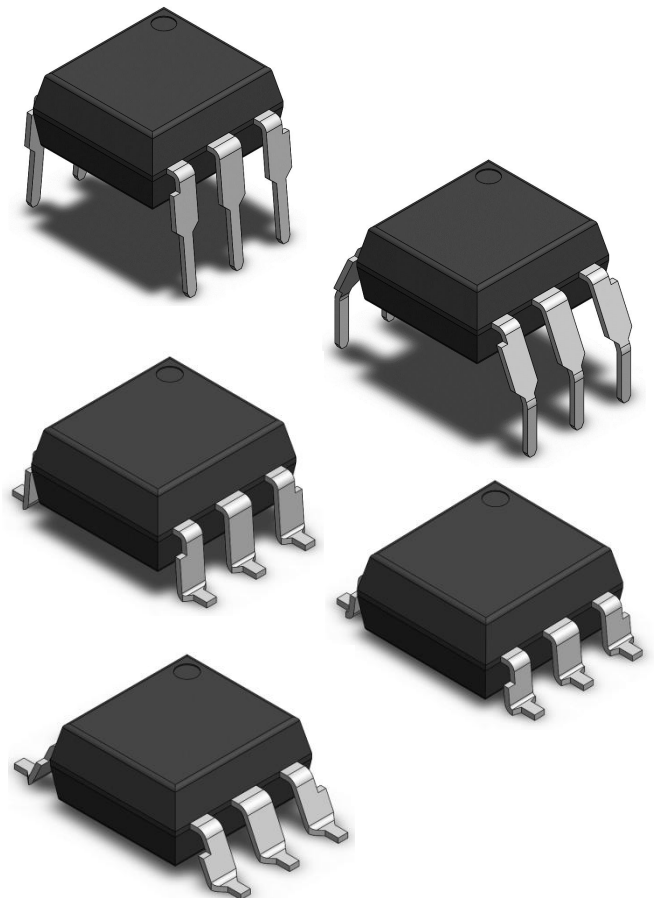
## SCHEMATIC



## PIN DEFINITION

<b>1. Anode</b>	<b>6. Base</b>
<b>2. Cathode</b>	<b>5. Collector</b>
<b>3. NC</b>	<b>4. Emitter</b>

## PACKAGE OUTLINE





**DIP6, DC Input, Photo Transistor Coupler**

<b>ABSOLUTE MAXIMUM RATINGS</b>				
PARAMETER	SYMBOL	VALUE	UNIT	NOTE
<b>INPUT</b>				
Forward Current	$I_F$	60	mA	
Peak Forward Current( $t=10\mu s$ )	$I_{FM}$	1	A	1
Reverse Voltage	$V_R$	6	V	
Power Dissipation( $T_A=25^\circ C$ )	$P_D$	120	mW	
<b>OUTPUT</b>				
Collector - Emitter Voltage	$V_{CEO}$	55	V	
Collector-Base Breakdown Voltage	$V_{CBO}$	55	V	
Emitter - Collector Voltage	$V_{ECO}$	7	V	
Emitter-Base Breakdown Voltage	$V_{EBO}$	7	V	
Collector Current	$I_C$	150	mA	
Power Dissipation( $T_A=25^\circ C$ )	$P_C$	150	mW	
<b>COMMON</b>				
Total Power Dissipation	$P_{tot}$	200	mW	
Isolation Voltage	$V_{iso}$	5000	Vrms	2
Operating Temperature	$T_{opr}$	-55~+110	$^\circ C$	
Storage Temperature	$T_{stg}$	-55~+110	$^\circ C$	
Soldering Temperature	$T_{sol}$	260	$^\circ C$	

Note 1. AC For 1 Minute, R.H. = 40 ~ 60%

Note 2. For 10 seconds



**DIP6, DC Input, Photo Transistor Coupler**

<b>ELECTRICAL OPTICAL CHARACTERISTICS at Ta=25°C</b>							
PARAMETER	SYMBOL	MIN	TYP.	MAX	UNIT	TEST CONDITION	NOTE
<b>INPUT</b>							
Forward Voltage	VF	/	-	1.24	1.4	V	IF=10mA
		H11B3	-	1.4	1.5	V	IF=50mA
Reverse Current	IR	-	-	10	μA	VR=6V	
Input Capacitance	Cin	-	50	-	pF	V=0, f=1kHz	
<b>OUTPUT</b>							
Collector Dark Current	ICEO	-	-	100	nA	VCE=10V	
Collector-Emitter Breakdown Voltage	BVCEO	55	-	-	V	IC=0.1mA	
Collector-Base Breakdown Voltage	BVCBO	55	-	-	V	IC=0.1mA	
Emitter-Collector Breakdown Voltage	BVECO	7	-	-	V	IE=0.1mA	



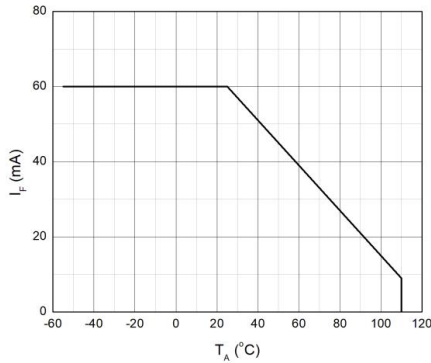
**DIP6, DC Input, Photo Transistor Coupler**

TRANSFER CHARACTERISTICS							
Current Transfer Ratio	CTR	4N31	50	-	-	%	IF=10mA, VCE=10V
		4N29,4N30	100	-	-		
		4N32,4N33	500	-	-		
		H11B1	500	-	-		IF=1mA, VCE=5V
		H11B2	200	-	-		
		H11B3	100	-	-		
		H11B255	100	-	-		
Collector-Emitt er Saturation Voltage	V <sub>CE(sat)</sub>	4N29,4N30, 4N32,4N33	-	-	1.0	V	IF= 8mA, IC= 2mA
		4N31	-	-	1.2		IF= 8mA, IC= 2mA
		H11B1,H11B2 H11B3	-	-	1.0		IF= 1mA, IC= 1mA
		H11B255	-	-	1.0		IF= 50mA, IC= 50mA
Isolation Resistance	R <sub>IO</sub>	10 <sup>11</sup>	-	-	Ω	V <sub>IO</sub> =500Vdc.	
Floating Capacitance	C <sub>IO</sub>	-	0.8	-	pF	V=0, f=1MHz	
Turn On Time	t <sub>on</sub>	H11B1,H11B2 H11B3, H11B255	-	25	-	μs	IC= 10mA, VCC= 2V, RL= 100Ω
		4N29,4N30, 4N31,4N32 4N33	-	-	5	μs	IC= 10mA, VCC= 2V, RL= 100Ω
Turn Off Time	t <sub>off</sub>	H11B1,H11B2 H11B3, H11B255	-	18	-	μs	IC= 10mA, VCC= 2V, RL= 100Ω
		4N32,4N33	-	-	100	μs	IC= 10mA, VCC= 2V, RL= 100Ω
		4N29,4N30, 4N31	-	-	40	μs	

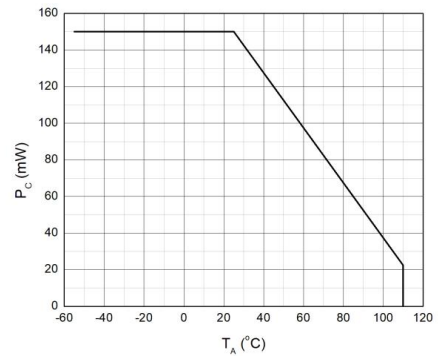


**CHARACTERISTIC CURVES**

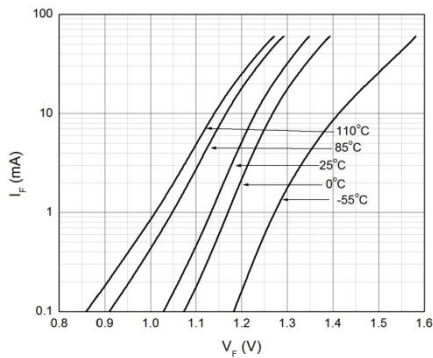
**Fig.1 Forward Current vs. Ambient Temperature**



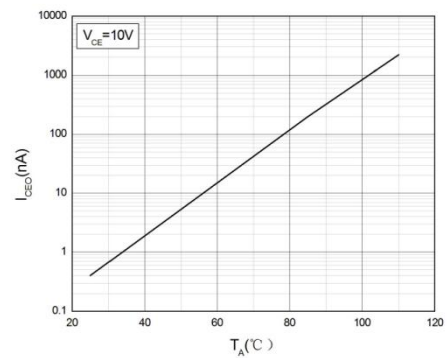
**Fig.2 Collector Power Dissipation vs. Ambient Temperature**



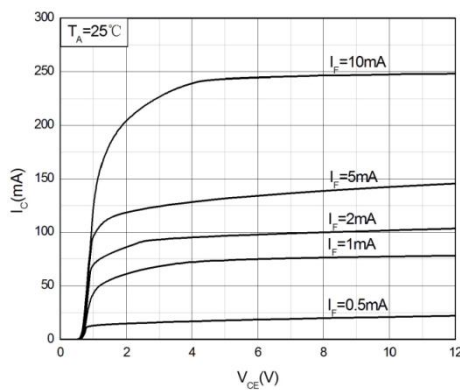
**Fig.3 Forward Current vs. Forward Voltage**



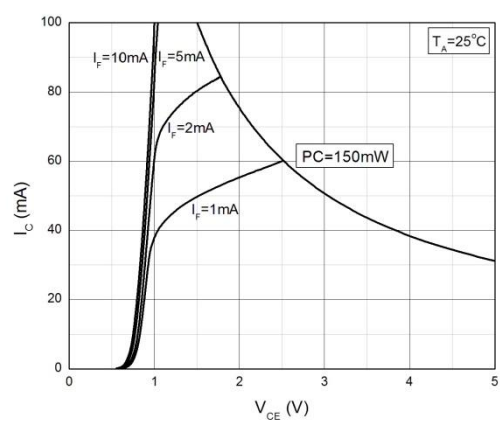
**Fig.4 Collector Dark Current vs. Ambient Temperature**



**Fig.5 Collector Current vs. Collector-emitter Voltage**



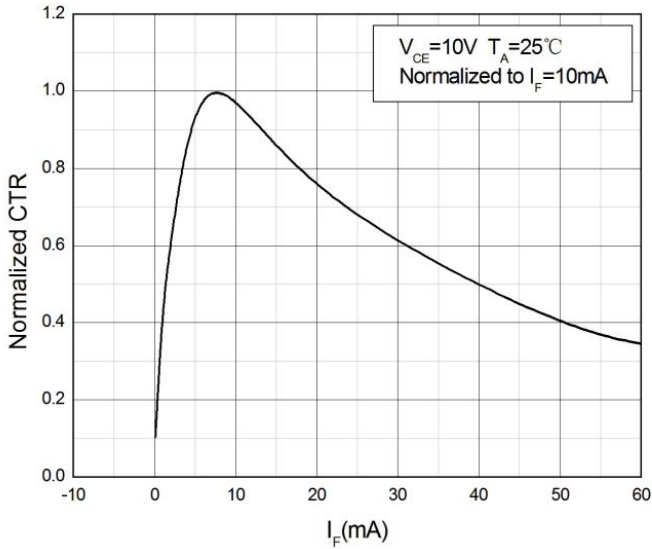
**Fig.6 Collector Current vs. Collector-emitter Voltage**



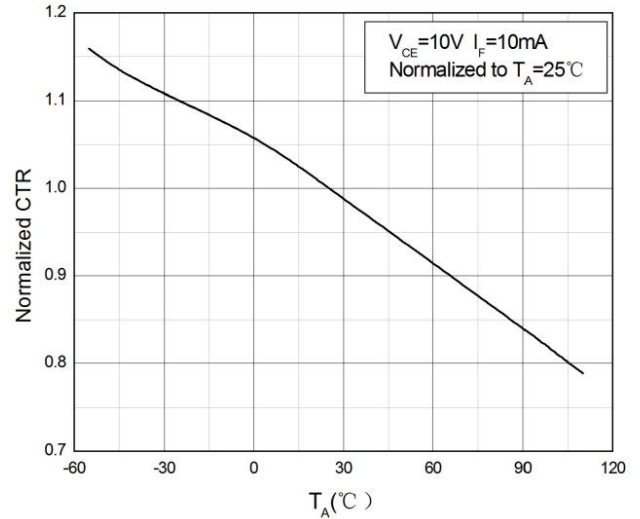


**CHARACTERISTIC CURVES**

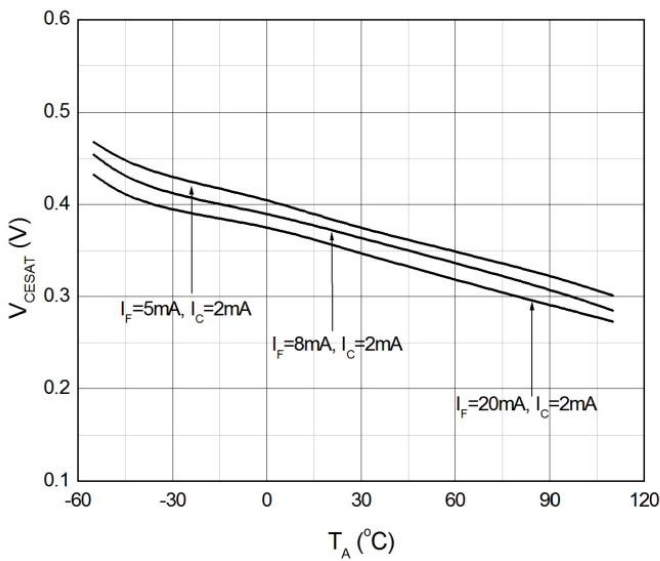
**Fig.7 Normalized Current Transfer Ratio vs. Forward Current**



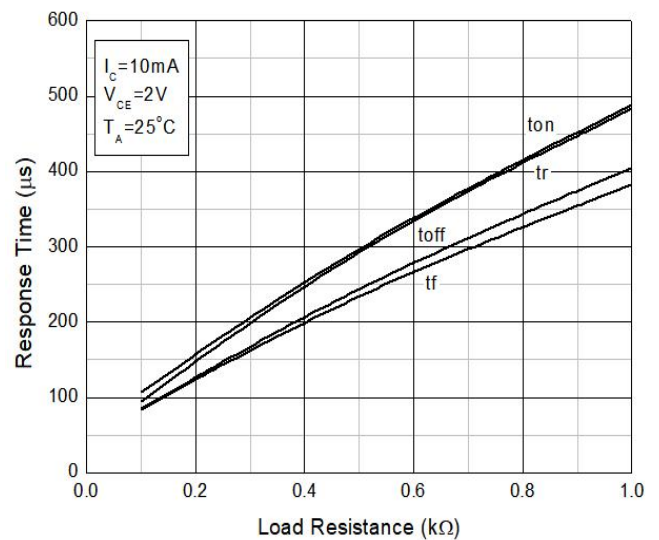
**Fig.8 Normalized Current Transfer Ratio vs. Ambient Temperature**



**Fig.9 Collector-emitter Saturation Voltage vs. Ambient Temperature**

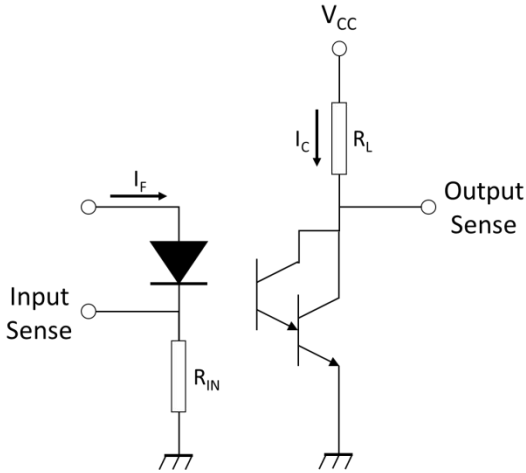


**Fig.10 Switching Time vs. Load Resistance**

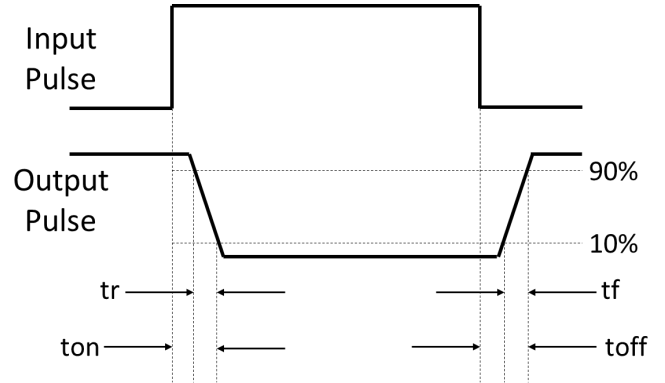


**TEST CIRCUITS**

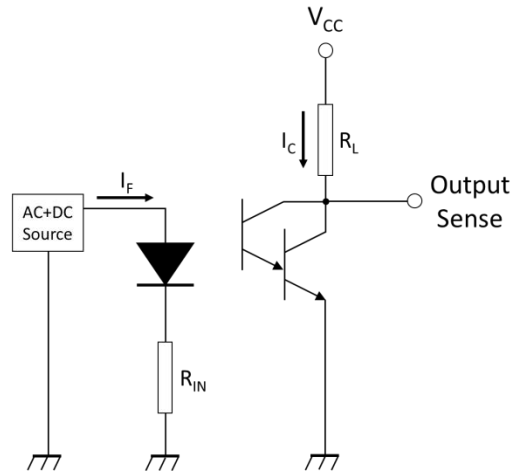
**Fig.11 Test Circuits of Response Time**



**Fig.12 Curves of Response Time**

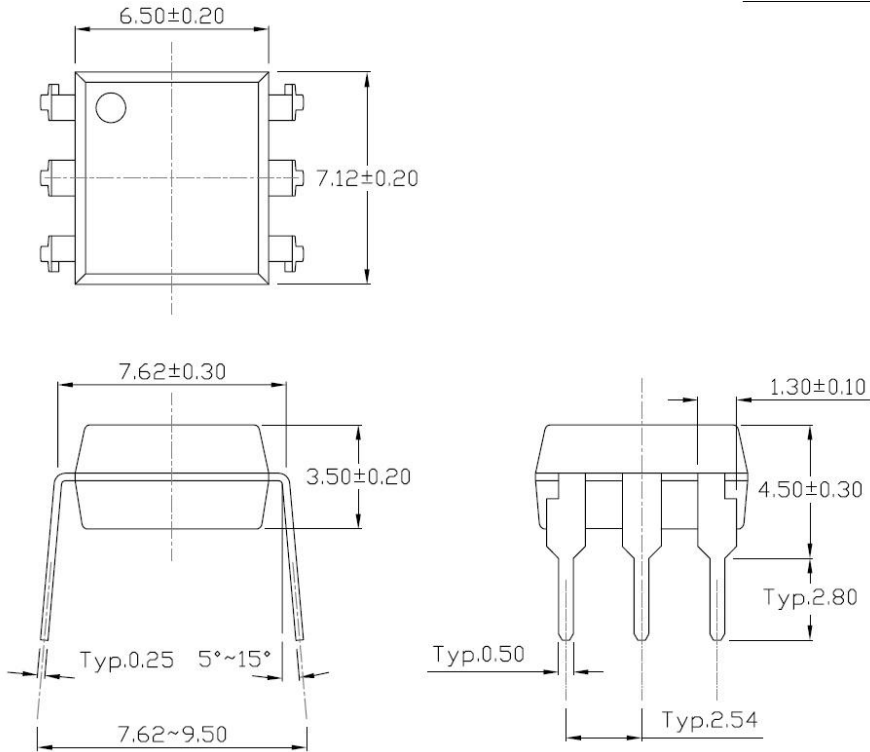


**Fig.13 Test Circuits of Frequency Response**

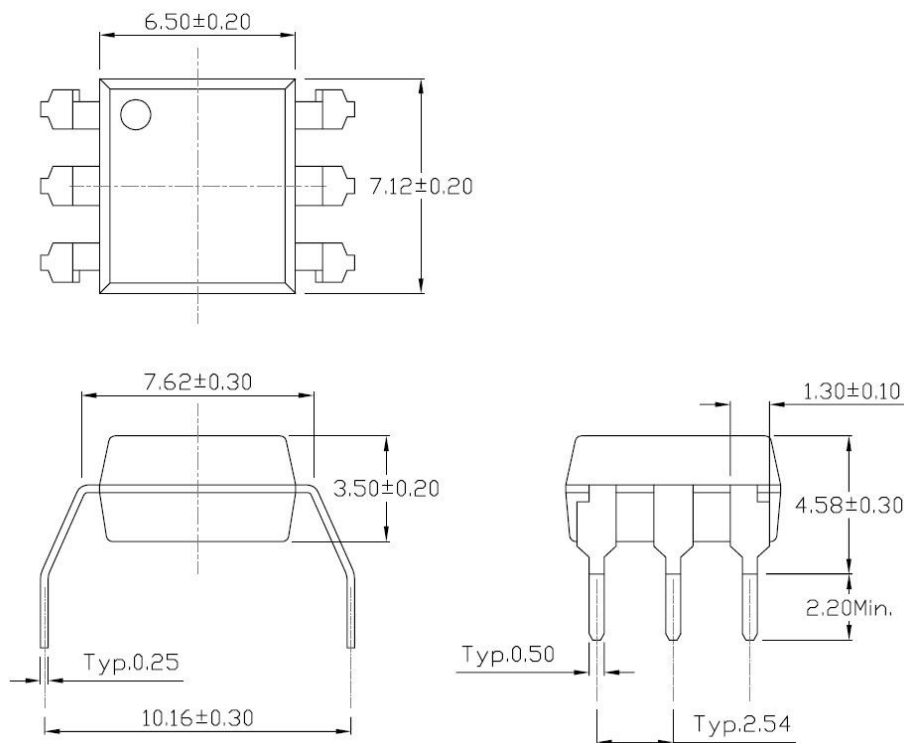


**PACKAGE DIMENSIONS (Dimensions in mm unless otherwise stated)**

**Standard DIP – Through Hole (DIP Type)**



**Gullwing (400mil) Lead Forming – Through Hole (M Type)**

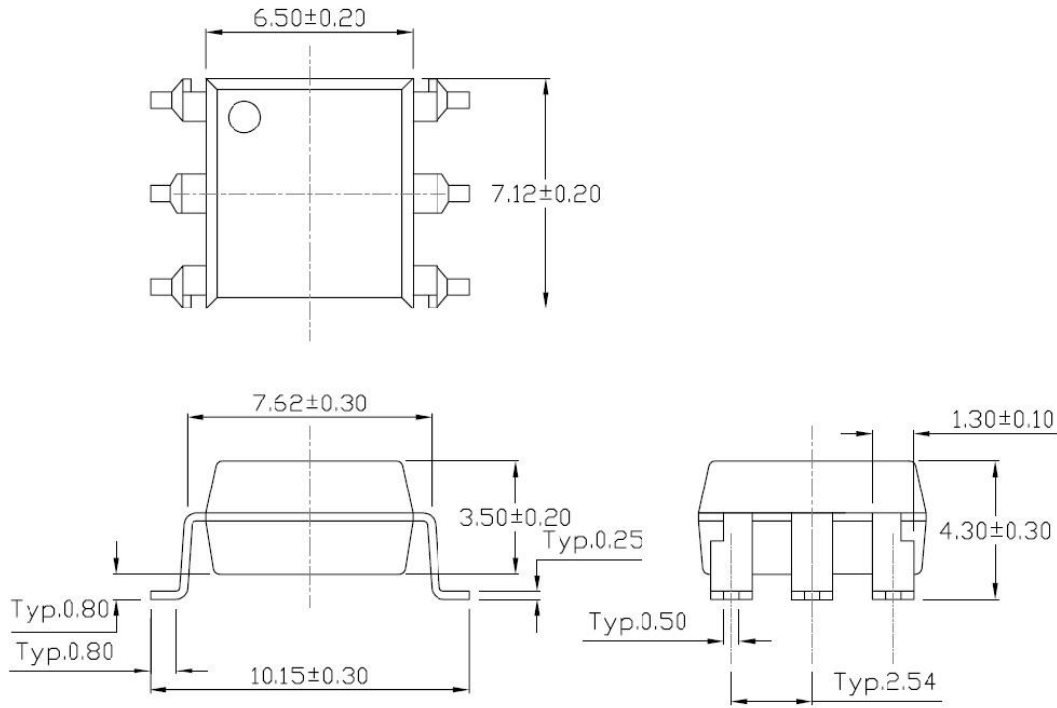






**PACKAGE DIMENSIONS (Dimensions in mm unless otherwise stated)**

**Surface Mount Lead Forming (S Type)**



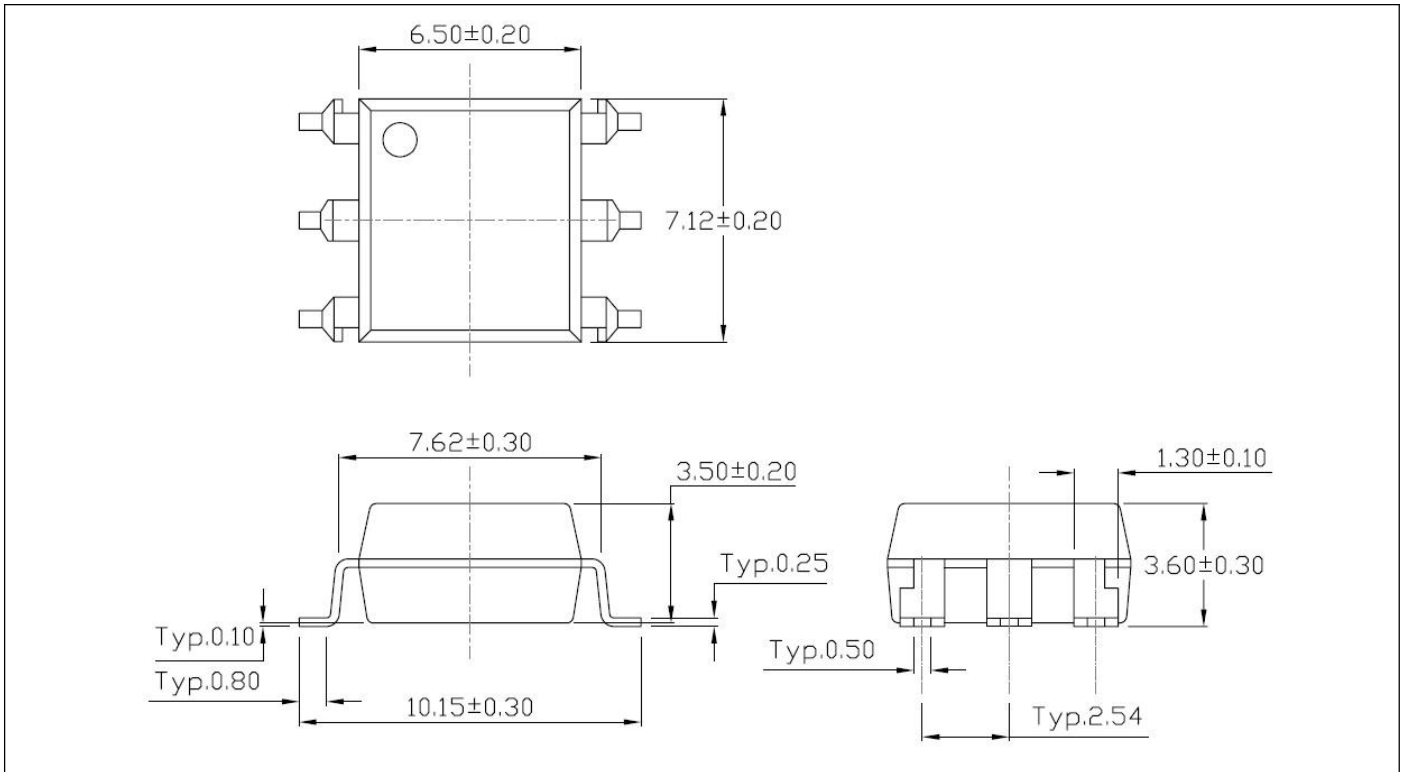
**Surface Mount (Low Profile) Lead Forming (SL Type)**



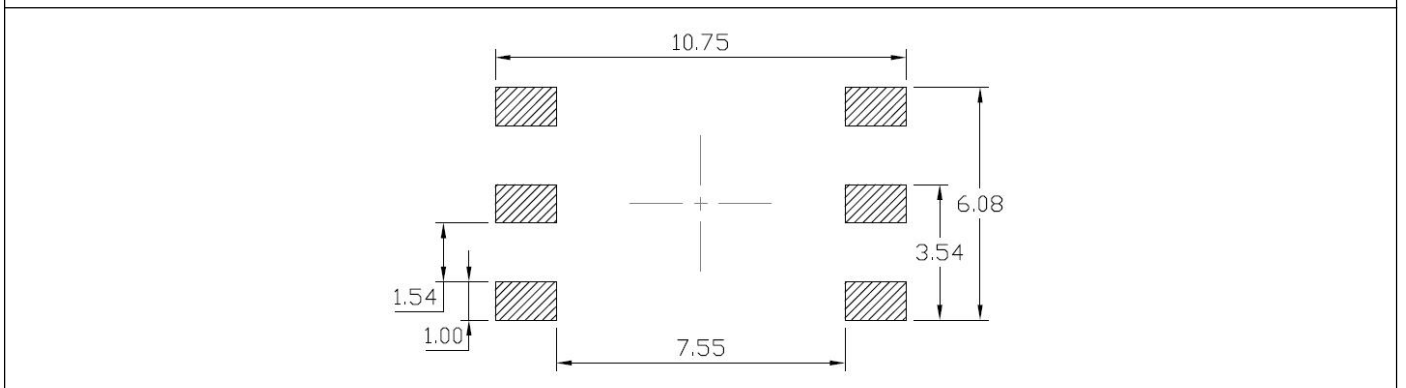
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**4N29, 4N30, 4N31, 4N32, 4N33,  
H11B1, H11B2, H11B3, H11B255**

**DIP6, DC Input, Photo Transistor Coupler**

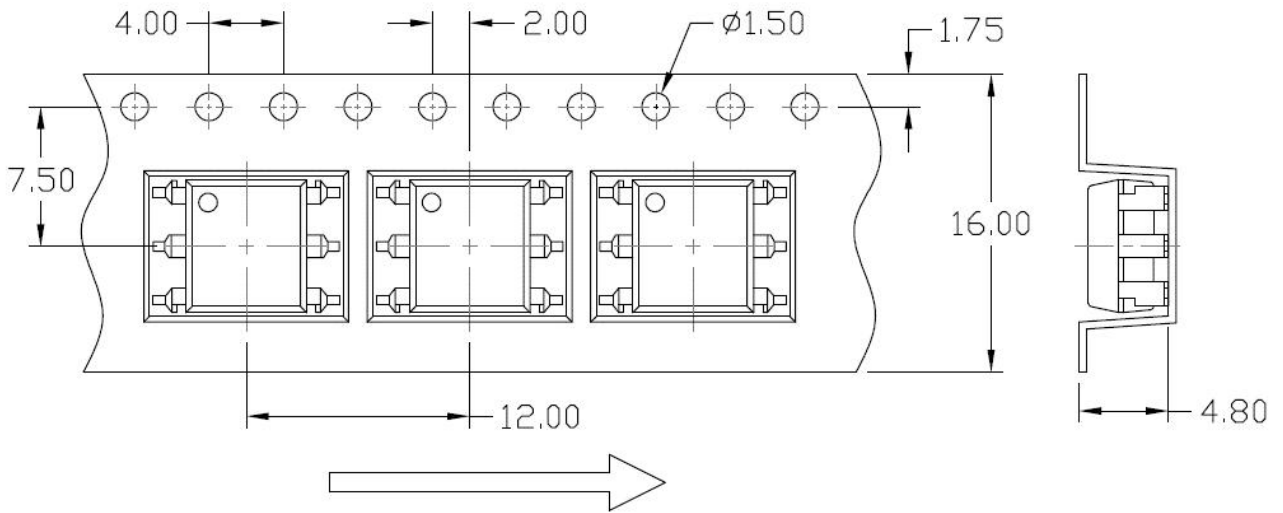


**Recommended Solder Mask (Dimensions in mm unless otherwise stated)  
Surface Mount Lead Forming & Surface Mount (Low Profile) Lead Forming**

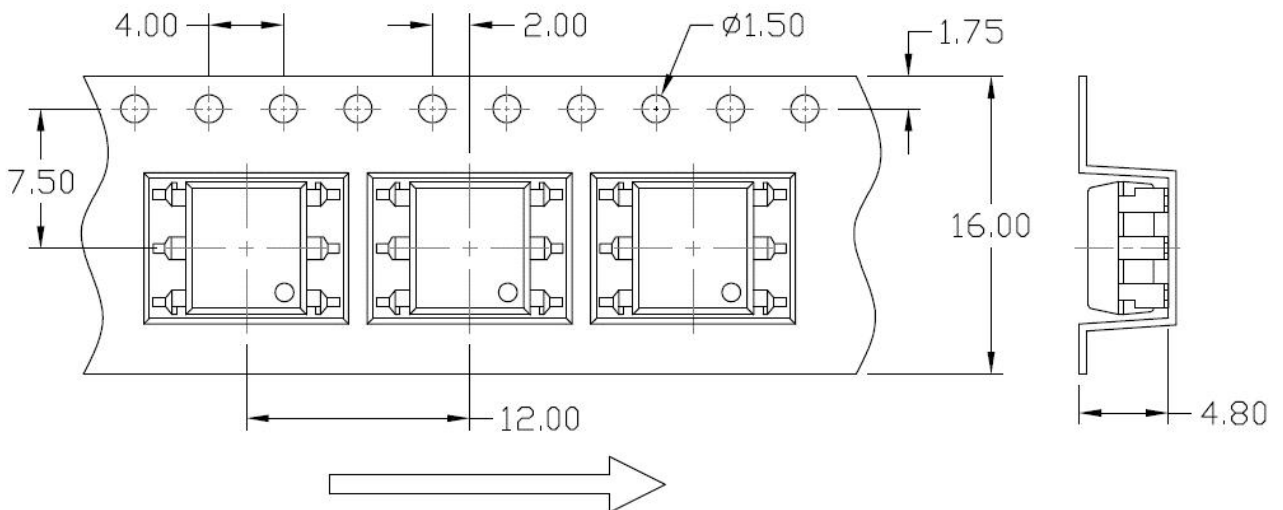


**Carrier Tape Specifications (Dimensions in mm unless otherwise stated)**

**Option S(T1) & SL(T1)**



**Option S(T2) & SL(T2)**





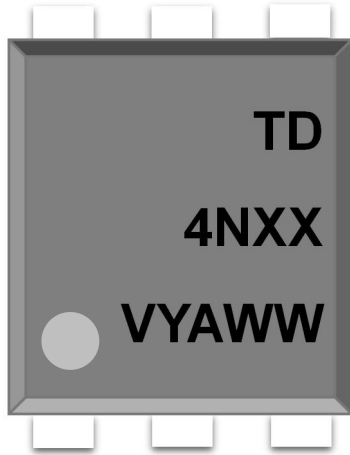
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**4N29, 4N30, 4N31, 4N32, 4N33,  
H11B1, H11B2, H11B3, H11B255**

**DIP6, DC Input, Photo Transistor Coupler**

**ORDERING AND MARKING INFORMATION**

**MARKING INFORMATION**



**TD** : Company Abbr.  
**4NXX** : Part Number & Rank  
**V** : VDE Option  
**Y** : Fiscal Year  
**A** : Manufacturing Code  
**WW** : Work Week

**ORDERING INFORMATION**

**LABEL INFORMATION**



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**4N29, 4N30, 4N31, 4N32, 4N33,  
H11B1,H11B2,H11B3,H11B255**

**DIP6, DC Input, Photo Transistor Coupler**

**4NXX(Y)(Z)-GV**

**H11BX(Y)(Z)-GV**

TD – Company Abbr.

4NXX/ – Part Number and Rank  
(XX=29/30/31/32/33)

H11BX/ – Part Number and Rank  
(X=1/2/3/255)

Y – Lead Form Option  
(M/S/SL/SLM/None)

Z – Tape and Reel Option (T1/T2)

G – Material Option

(G: Green, None: Non-Green)

V – VDE Option (V or None)

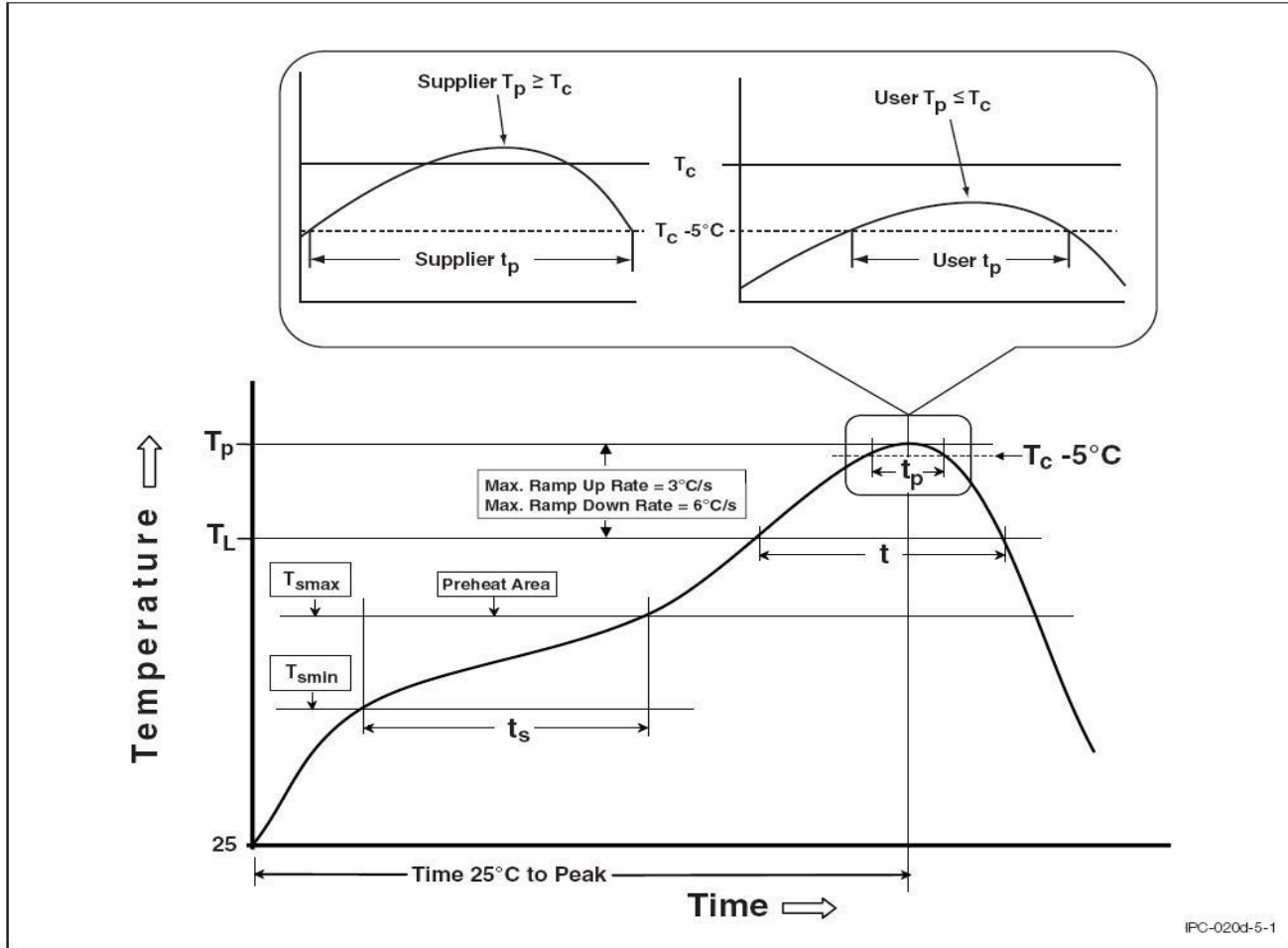


**PACKING QUANTITY**

Option	Description	Quantity
None	Standard 6 Pin Dip	50Units/Tube
M	Gullwing(400mil) Lead Forming	50Units/Tube
S(T1)	Surface Mount Lead Forming – With Option 1 Taping	1000 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option 2 Taping	1000 Units/Reel
SL(T1)	Surface Mount Lead Forming(Low Profile) – With Option 1 Taping	1000 Units/Reel
SL(T2)	Surface Mount Lead Forming(Low Profile) – With Option 2 Taping	1000 Units/Reel

**REFLOW INFORMATION**

**REFLOW PROFILE**



IPC-0203-5-1

Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. ( $T_{smin}$ )	100	150°C
Temperature Max. ( $T_{smax}$ )	150	200°C
Time ( $t_s$ ) from ( $T_{smin}$ to $T_{smax}$ )	60-120 seconds	60-120 seconds
Ramp-up Rate ( $t_L$ to $t_P$ )	3°C/second max.	3°C/second max.
Liquidous Temperature ( $T_L$ )	183°C	217°C
Time ( $t_L$ ) Maintained Above ( $T_L$ )	60 – 150 seconds	60 – 150 seconds
Peak Body Package Temperature	235°C +0°C / -5°C	260°C +0°C / -5°C
Time ( $t_P$ ) within 5°C of 260°C	20 seconds	30 seconds
Ramp-down Rate ( $T_P$ to $T_L$ )	6°C/second max	6°C/second max
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.



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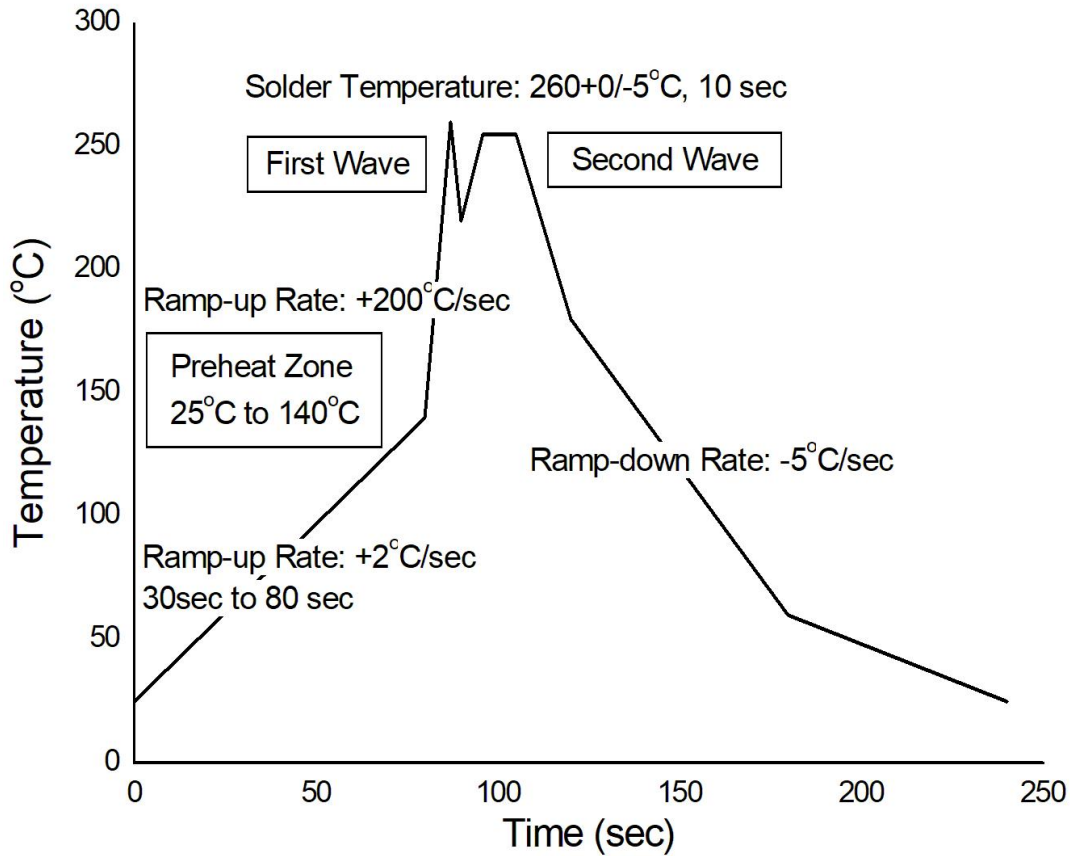
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***DIP6, DC Input, Photo Transistor Coupler***



**TEMPERATURE PROFILE OF SOLDERING**

**WAVE SOLDERING (JESD22-A111 COMPLIANT)**



**HAND SOLDERING BY SOLDERING IRON**

Soldering Temperature	380+0/-5°C
Soldering Time	3 sec max.

- One time soldering is recommended for all soldering method.
- Do not solder more than three times for IR reflow soldering.





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- This product is not intended to be used for military, aircraft, automotive, medical, life sustaining or lifesaving applications or any other application which can result in human injury or death.
- Please contact LIGHTNING sales agent for special application request.
- Immerge unit's body in solder paste is not recommended.
- Parameters provided in datasheets may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated in each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify LIGHTNING's terms and conditions of purchase, including but not limited to the warranty expressed therein.
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